

Please amend the paragraph starting on page 2, line 5 to state:

B1 "To remedy the drawbacks of the above masking process, a process has recently been proposed in which a non-uniform thickness oxide layer is grown in a single step. This process includes forming, on the surface of the substrate, predetermined regions having an oxidation rate reduced by nitrogen ion implantation in these predetermined regions, at points where it is desired to obtain a thinner oxide layer, and then growing a silicon oxide layer by oxidation of the surface of the silicon substrate. Such a process is described in the article "Formation of Ultrathin Nitrided SiO₂ Oxides by Direct Nitrogen Implantation into Silicon", by H.R. Soleimani, B.S. Doyle and A. Philipossian, J. Electrochem. Soc., Vol. 142, No. 8, August 1998."

PAGE 4.

Please amend Table 1 to read as set forth below:

B2 **TABLE 1**
Thickness of oxide layer formed, nm

Implanted Dose	Implantation Energy		
	2 keV	10 keV	80 keV
5×10^{13} at/ cm ²	4.78	5.74	-
5×10^{14} at/ cm ²	5.66	5.92	6.0
5×10^{15} at/ cm ²	6.01	6.75	-
5×10^{16} at/ cm ²	8.8	12.3	11.0

[Please amend the paragraph starting on page 4, line 21 to state:]

"By way of comparison, the thickness of the oxide layer obtained under the same oxidation conditions on a similar silicon wafer that has not undergone implantation is 4.7 nm."